

10/540263

JC17 Rec'd PCT/PTO 23 JUN 2005

00862.102566.

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	
KIYOFUMI SAKAGUCHI, ET AL.)	Examiner: Not Yet Assigned
Application No.: Not Yet Assigned)	Group Art Unit: Not Yet Assigned
Filed: Herewith)	:
For: SEMICONDUCTOR SUBSTRATE,)	
MANUFACTURING METHOD)	
THEREOF, AND)	
SEMICONDUCTOR DEVICE)	June 22, 2005

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the non-U.S. documents listed on the enclosed Form PTO-1449. Copies of the listed documents are also enclosed.

For a concise explanation of relevance of the non-English documents, the Examiner is referred to the enclosed English-language abstracts, and to pages 2 and 13 of the specification.

Some of the listed documents were cited in a PCT International Search Report mailed February 8, 2005 for International Application No. PCT/JP2004/018982, which is the parent of the present application from which this application claims priority. A copy of this search report is also enclosed.

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Some of the listed documents were cited in a PCT International Search Report mailed March 29, 2005 for International Application No. PCT/JP2004/018981, which is the parent of the present application from which this application claims priority. A copy of this search report is also enclosed.

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our address given below.

Respectfully submitted,



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Attorney for Applicants
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FORM PTO 1449 (modified) • U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)			ATTY DOCKET NO. 00862.102566.		APPLICATION NO. 23 JUN 2005 107940263		
			APPLICANT KIYOFUMI SAKAGUCHI, ET AL. KUMONI				
			FILING DATE HEREWITH			GROUP NOT YET ASSIGNED	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,221,413	06/22/93	Brasen, et al.	117	89	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
	JPA	2003-78118	03/14/03	Japan			Abstract
	JPA	2003-78140	03/14/03	Japan			Abstract
	JPA	2003-178977	06/27/03	Japan			Abstract
	JPA	2003-282464	10/03/03	Japan			Abstract
	JPA	2003-282463	10/03/03	Japan			Abstract
	JPA	2004-342975	12/02/04	Japan			Abstract
	JPA	11-195562	07/21/99	Japan			Abstract
	JPA	07-302889	11/14/95	Japan			Abstract
	EP	1248294 A2	10/09/02	EPO			
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
	Current, I, Michael., et al. "Atomic-Layer Cleaving with Si₃Ge₂ Strain Layers For Fabrication of Si and Ge-rich SOI Device Layers" IEEE International SOI Conference, October 1, 2001, pp. 11-12.						
	Shin-ichi Takagi, "Metal-Oxide-Semiconductor (MOS) device technologies using Si/Ge heretointerfaces", Oyo Buturi, Vol. 72, NO. 3, pp. 284-290, 2003.						
	T.A. Langdo, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 4256-4258 (2003).						
	D.J. Godbey, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 373-379 (1990).						
	D. Ferijoo, et al., J. Electro. Mat., vol. 23, no. 6, pp. 493-496 (1994).						
	A.H. Krist, et al., Appl. Phys. Lett., vol. 58, no. 17, pp. 1899-1901 (1991).						
EXAMINER				DATE CONSIDERED			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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